

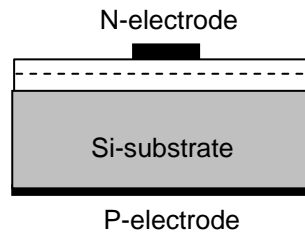
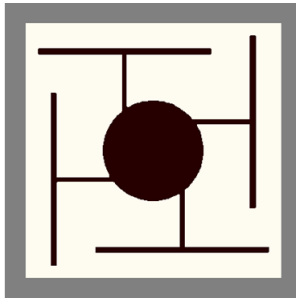
### > Mechanical Specification:

#### (1) Dimension

- Chip size: 14 mil x 14 mil ( $340\pm 25\ \mu\text{m}$  x  $340\pm 25\ \mu\text{m}$ )
- Thickness: 8.8 mil ( $225\pm 25\ \mu\text{m}$ )
- N bonding pad: 4.5mil ( $115\pm 10\ \mu\text{m}$ )

#### (2) Metallization

- Topside N electrode: Au alloy
- Backside P electrode: Au alloy



#### Features:

- Long-term supply
- High luminous intensity
- Thin film structure
- Vertical electrode
- High driving current

#### Applications:

- Automotive

### > Electro-optical Characteristics at 25°C:

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit	
Forward Voltage	Vf1	If = 10 $\mu$ A	1.3	-	-	V	
	Vf2	If = 20mA	-	2.1	2.5	V	
Reverse Current	Ir	Vr = 25V	-	-	5.0	$\mu$ A	
Peak Wavelength	$\lambda_p$	If = 20mA	-	621	-	nm	
Dominant Wavelength <sup>(1)</sup>	$\lambda_d$	If = 20mA	610	-	620	nm	
Spectra Half-width	$\Delta\lambda$	If = 20mA	-	18	-	nm	
Luminous Intensity <sup>(2)(3)</sup>	Iv	E23	If = 20mA	950	-	-	mcd
		E24		1050	-	-	
		E25		1150	-	-	
		E26		1250	-	-	

Note:

(1) Basically, the wavelength span is 10nm; however, customers' special requirements are also welcome.

(2) Customers' special requirements are also welcome.

(3) Luminous intensity is measured by EPISTAR's equipment on bare chips.

## > Absolute Maximum Ratings<sup>(1)</sup>:

Parameter	Symbol	Condition	Rating	Unit
Forward DC Current	I <sub>f</sub>	T <sub>a</sub> = 25°C	≤ 70	mA
Reverse Voltage	V <sub>r</sub>	T <sub>a</sub> = 25°C	≤ 10	V
Junction Temperature	T <sub>j</sub>	-	≤ 125	°C
ESD withstand voltage(HBM) <sup>(2)</sup>	V <sub>ESD</sub>	-	Up to 2	kV
Storage Temperature	T <sub>stg</sub>	Chip	-40 ~ +85	°C
		Chip-on-tape/storage	5 ~ 35	°C
		Chip-on-tape/transportation	-20 ~ +65	°C
Temperature during Packaging	-	-	280(<10sec)	°C

Note: (1)Maximum ratings are package dependent. The above maximum ratings were determined using a Printed Circuit Board (PCB) without an encapsulant. Stresses in excess of the absolute maximum ratings such as forward current and junction temperature may cause damage to the LED.

(2)According to ANSI/ESDA/JEDEC JS-001

## > Characteristic Curves:

Fig.1 – Relative luminous Intensity vs. Forward Current

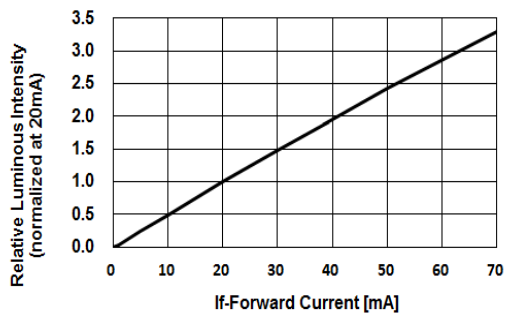


Fig.2 – Forward Current vs. Forward Voltage

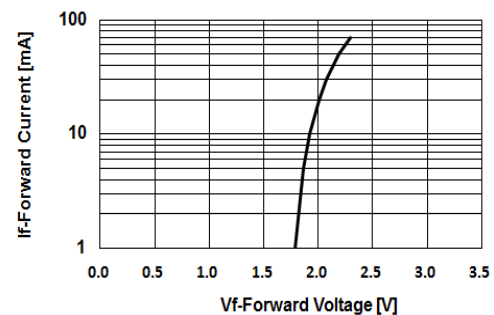


Fig.3 – Relative Intensity (@20mA) vs. Ambient Temperature

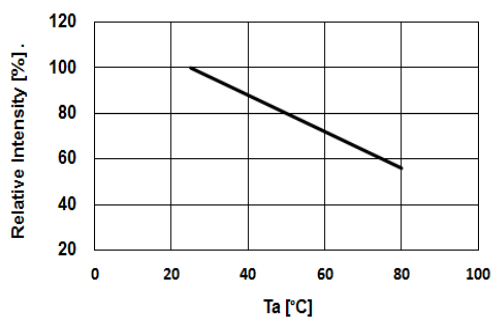


Fig.4 – Forward Voltage (@20mA) vs. Ambient Temperature

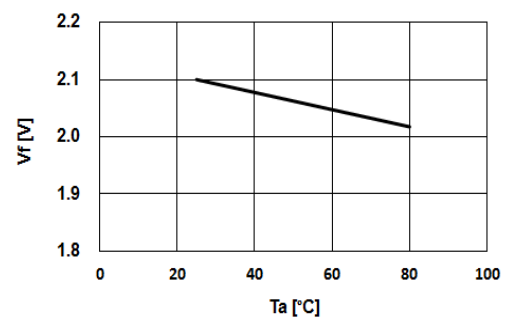


Fig.5 – Dominant Wavelength (@20mA) vs. Ambient Temperature

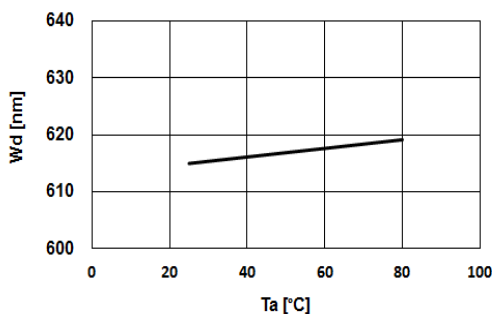
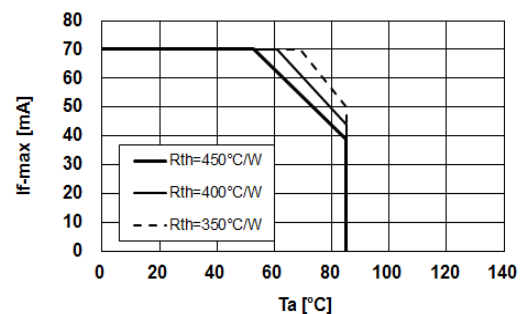


Fig.6 – Maximum Driving Forward DC Current vs. Ambient Temperature (De-rating based on T<sub>j</sub> max. = 125°C)



## > Qualification :

- <sup>1)</sup> EPSTAR's LED chips and epi-wafers are designed and manufactured according to the quality management system that complies to the IATF 16949:2016 requirements (IATF No: 0325277/ Certificate Registration No: 20000910 IATF16).
- <sup>2)</sup> The chip qualification test plan is based on the guidelines of AEC-Q101-REV-D, Failure Mechanism Based Stress Test Qualification for Discrete Semiconductors in Automotive Applications.

## > Revision :

Version	Page	Subjects	Date of Modification
A		Initial Release	Apr. 2017
B		Iv rank change (E22/E23/E24->E23/E24/E25/E26)	October. 2018
C	3	ISO/TS 16949:2009 Revision (IATF 16949:2016)	October. 2018